

## Silicon NPN Power Transistors

2SC2485

## DESCRIPTION

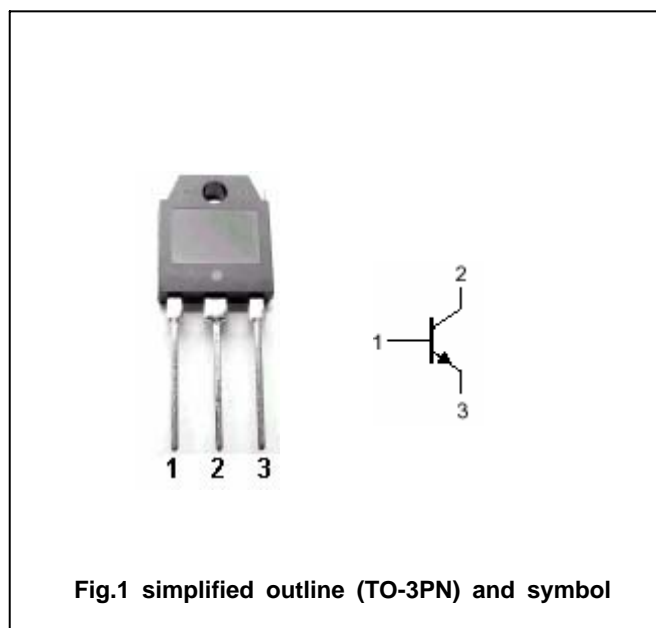
- With TO-3PN package
- Complement to type 2SA1061
- High collector power dissipation

## APPLICATIONS

- High power audio frequency amplifier

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	100	V
$V_{CEO}$	Collector-emitter voltage	Open base	100	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current (DC)		6	A
$I_{CP}$	Collector current (Pulse)		10	A
$P_C$	Collector power dissipation	$T_C=25$	70	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon NPN Power Transistors

## 2SC2485

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4A			2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =4A; V <sub>CE</sub> =5V			1.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =3V; I <sub>C</sub> =0			50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	40		200	
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V		20		MHz

◆ h<sub>FE-2</sub> Classifications

R	Q	P
40-80	60-120	100-200

Silicon NPN Power Transistors

2SC2485

PACKAGE OUTLINE

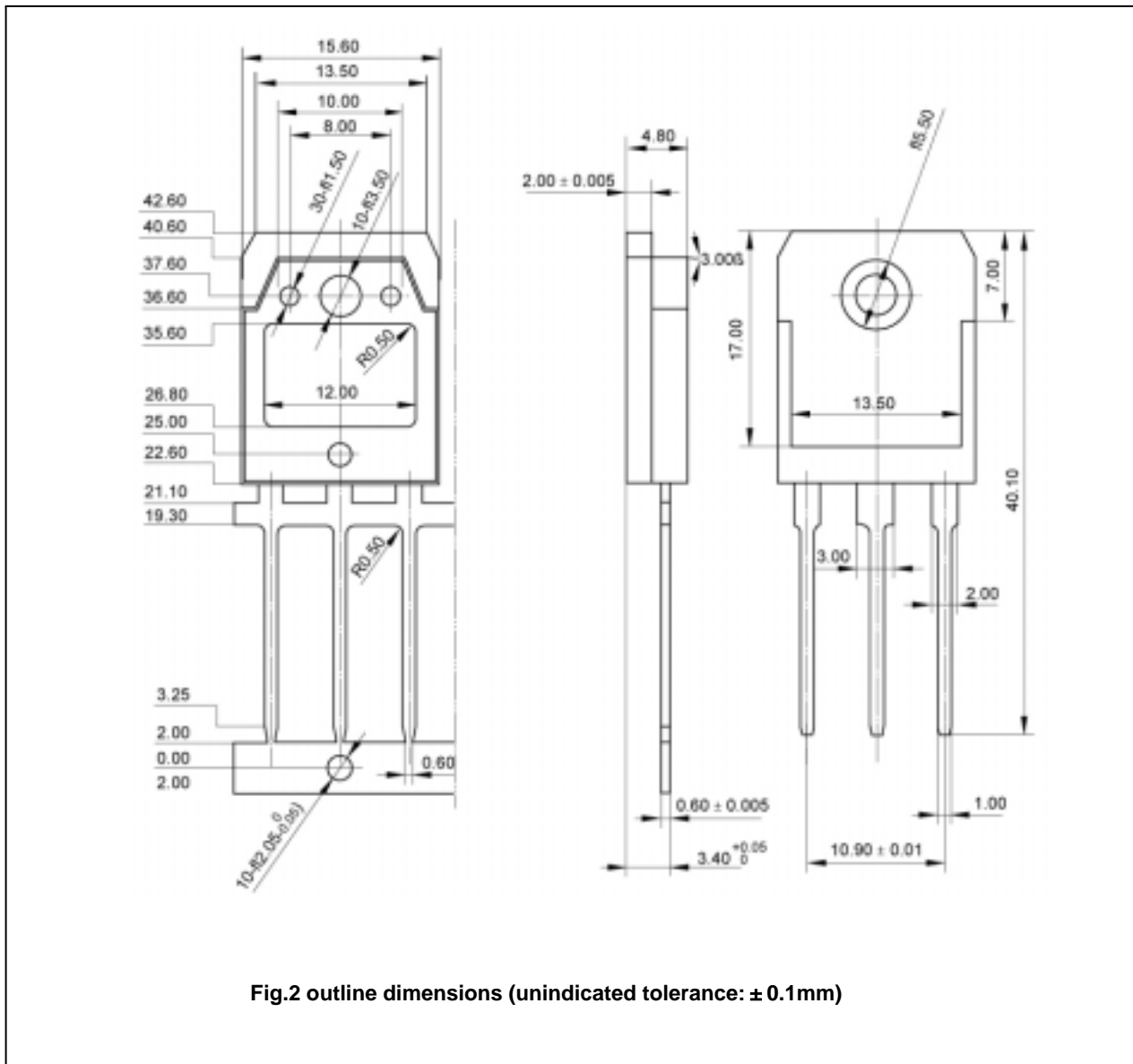


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)